

# **isc Silicon NPN Power Transistor**

# 2N6102

### DESCRIPTION

- DC Current Gain -
- : h<sub>FE</sub> = 20-80@ I<sub>C</sub>= 5A
- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub>= 40V(Min)

• Minimum Lot-to-Lot variations for robust device performance and reliable operation

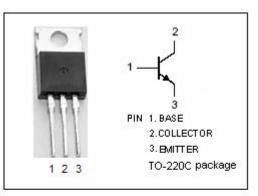
## APPLICATIONS

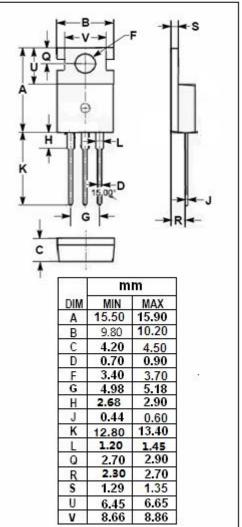
• Designed for use in general-purpose amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)						
SYMBOL PARAMETER		VALUE	UNIT			
V <sub>CBO</sub>	Collector-Base Voltage	45	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V			
V <sub>CER</sub>	Collector-Emitter Voltage R <sub>BE</sub> = 100 $\Omega$	45	V			
V <sub>EBO</sub>	Emitter-Base Voltage	5	V			
lc	Collector Current-Continuous	16	A			
IB	Base Current-Continuous	4	Α			
Pc	Collector Power Dissipation @ Tc=25°C	75	W			
TJ	Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C			

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.67	℃ <b>/W</b>
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	70	°C/W





isc website: <u>www.iscsemi.com</u>



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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
Vceo(sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	40		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 16A; I <sub>B</sub> = 3.2A		2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 8A ; V <sub>CE</sub> = 4V		1.7	V
ICEX	Collector Cutoff Current	V <sub>CE</sub> = 45V; V <sub>BE</sub> = -1.5V V <sub>CE</sub> = 40V; V <sub>BE</sub> = -1.5V;T <sub>C</sub> =150°C		2.0 10	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 40V;I <sub>B</sub> = 0		2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 8A ; V <sub>CE</sub> = 4V	15	60	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 16A ; V <sub>CE</sub> = 4V	5		

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